

SANYO	No.1800E	2SC3675
		NPN Triple Diffused Planar Silicon Transistor High-Voltage Amp, High-Voltage Switching Applications

Applications

- High-voltage amplifiers.
- High-voltage switching applications.
- Dynamic focus applications.

Features

- High breakdown voltage ($V_{CEO\ min} = 900V$).
- Small Cob (Cob typ = 2.8pF).
- Wide ASO (Adoption of MBIT process).
- High reliability (Adoption of HVP process).

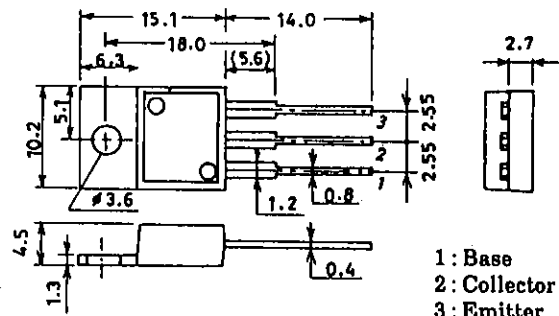
Absolute Maximum Ratings at $T_a = 25^\circ C$

Collector-to-Base Voltage	V_{CBO}		1500	V	unit
Collector-to-Emitter Voltage	V_{CEO}		900	V	
Emitter-to-Base Voltage	V_{EBO}		5	V	
Collector Current	I_C		100	mA	
Collector Current (Pulse)	I_{CP}		300	mA	
Collector Dissipation	P_C	$T_c = 25^\circ C$	10	W	
Junction Temperature	T_j		150	$^\circ C$	
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$	

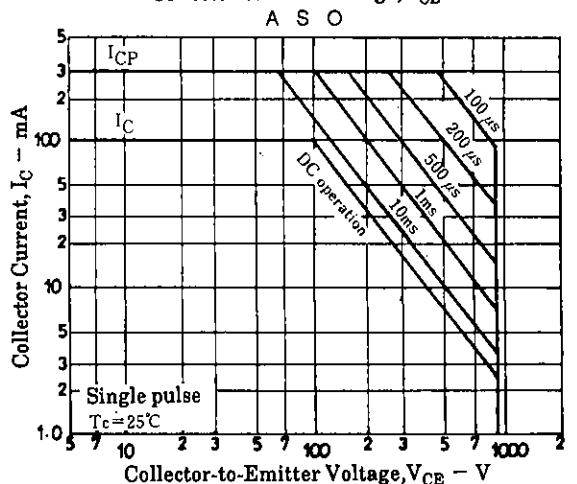
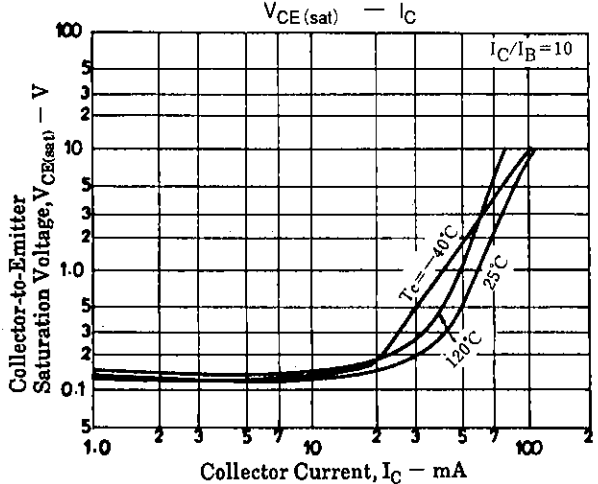
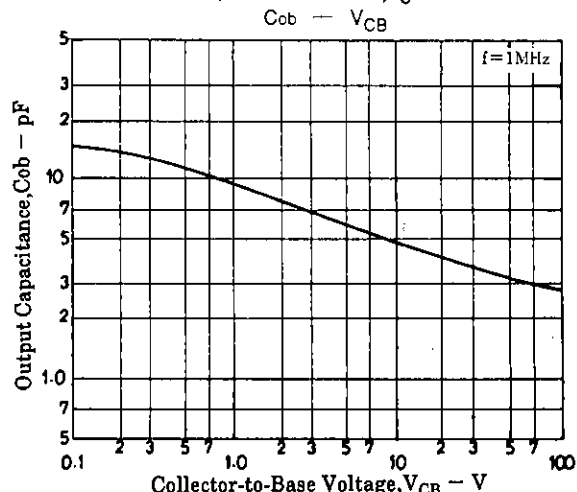
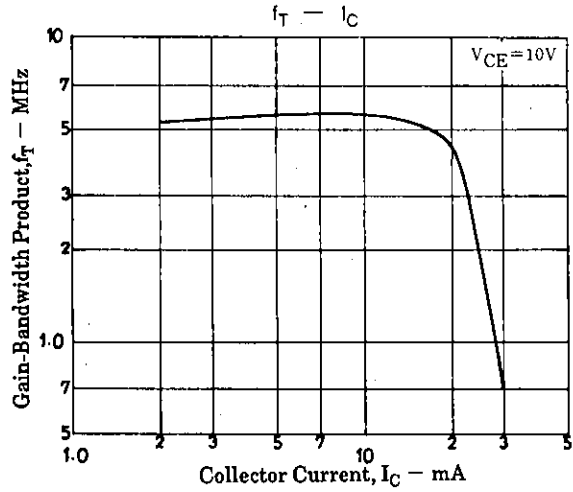
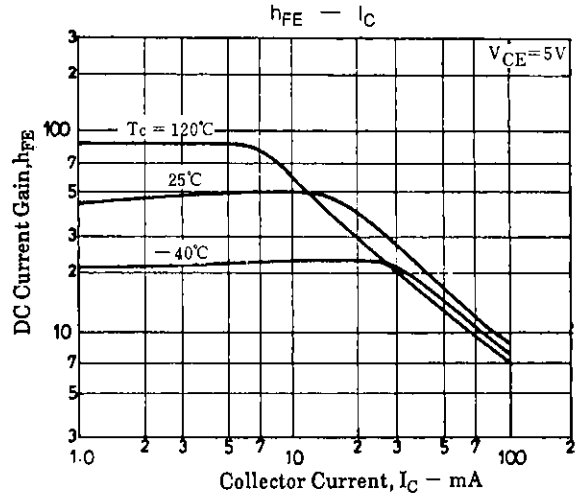
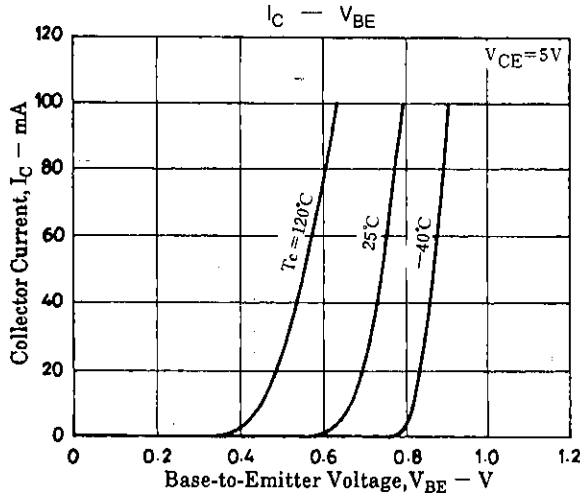
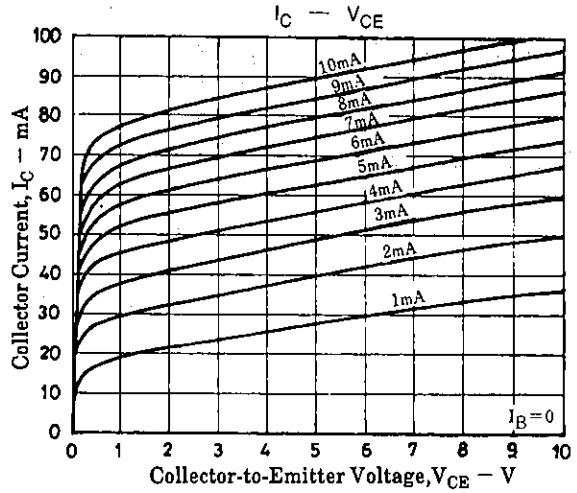
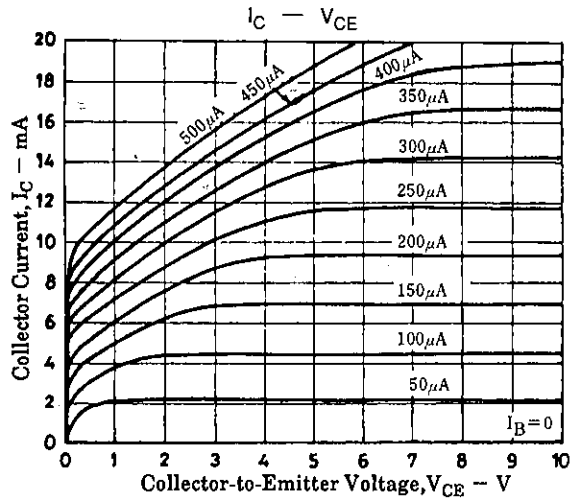
Electrical Characteristics at $T_a = 25^\circ C$

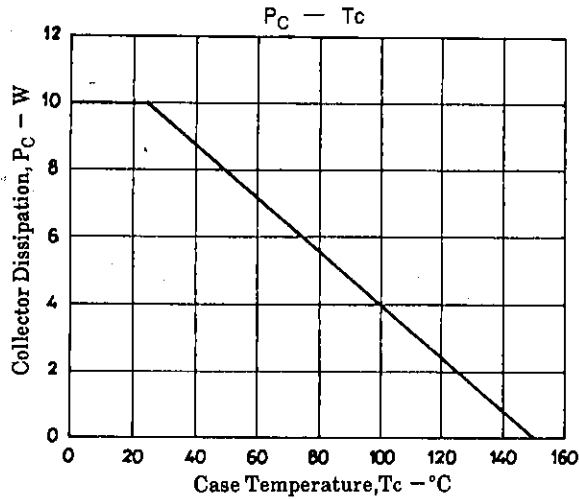
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 900V, I_E = 0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			10	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 10mA$	30			
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 10mA$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 4mA$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 20mA, I_B = 4mA$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1mA, I_E = 0$	1500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	900			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1mA, I_C = 0$	5			V
Output Capacitance	Cob	$V_{CB} = 100V, f = 1MHz$		2.8		pF

Package Dimensions 2010C
(unit: mm)



JEDEC: TO220AB
EIAJ: SC46





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